



**DMT12H007SPS** 

#### **120V N-CHANNEL ENHANCEMENT MODE MOSFET** PowerDI5060-8

#### Product Summary

BV <sub>DSS</sub>	Rds(on) Max	I <sub>D</sub> Tc = +25°С
120V	8.9mΩ @ V <sub>GS</sub> = 10V	80A
1200	16mΩ @ V <sub>GS</sub> = 6V	65A

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Switching
- **DC-DC** converters

#### Features

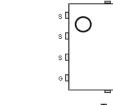
- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- Thermally Efficient Package Cooler Running Applications •
- High Conversion Efficiency
- Low RDS(ON) Minimizes On-State Losses
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.097 grams (Approximate)







S Internal Schematic

D

Top View Pin Configuration ΠD ħ٥

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ΠD

## Ordering Information (Note 4)

Part Number	Paakaga	Packing		
	Package	Qty.	Carrier	
DMT12H007SPS-13	PowerDI5060-8	2,500	Tape & Reel	

1. EU Directive 2002/95/EC (RoHS)	). 2011/65/EL	J (RoHS 2) & 2015/863/E	U (RoHS 3) compliant.	. All applicable RoH	S exemptions applied.	

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

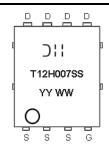
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3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**

Notes:



 $\Box$  = Manufacturer's Marking T12H007SS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 22 = 2022) WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Value	Unit
Drain-Source Voltage		VDSS	120	V
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 5)	T <sub>C</sub> = +25°C T <sub>C</sub> = +70°C	ID	80 64	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	·	IDM	320	A
Continuous Body Diode Forward Current (Note 5)	Tc = +25°C	ls	80	А
Pulsed Body Diode Forward Current (Note 5)	Tc = +25°C	lsм	320	A
Avalanche Current, L = 3mH		I <sub>AS</sub>	15.5	A
Avalanche Energy, L = 3mH		Eas	360.4	mJ

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	PD	2.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Reja	43	°C/W
Total Power Dissipation (Note 5)	PD	104	W
Thermal Resistance, Junction to Case (Note 5)	Rejc	1.2	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

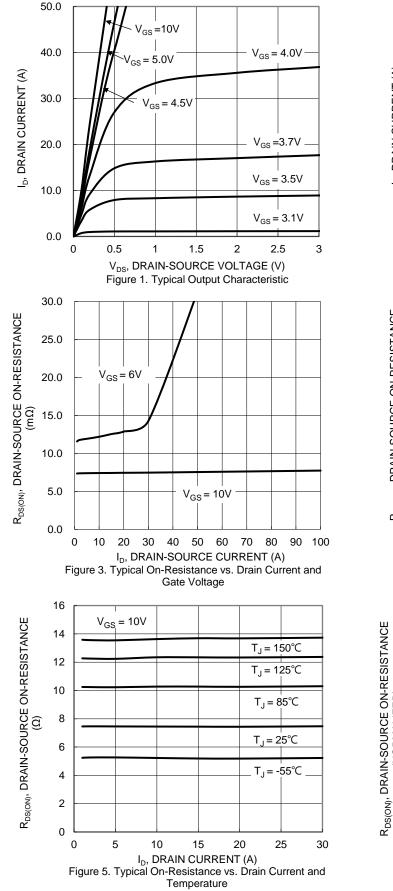
Characteristic	Symbol	Mim	Turn	Max	Unit	Test Condition	
	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			1	1	1		
Drain-Source Breakdown Voltage	BVDSS	120	—	—	V	$V_{GS} = 0V, I_D = 10mA$	
Zero Gate Voltage Drain Current	IDSS	_	—	1	μA	V <sub>DS</sub> = 96V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	lgss		—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	VGS(TH)	2	_	4	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Descent		7.5	8.9	mΩ	$V_{GS} = 10V, I_{D} = 30A$	
Static Drain-Source On-Resistance	Rds(on)	_	12	16	11177	$V_{GS} = 6V, I_D = 10A$	
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 30A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	3142	—		$V_{DS} = 60V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	_	665	—	pF		
Reverse Transfer Capacitance	Crss	—	29	—			
Gate Resistance	Rg	_	1.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge ( $V_{GS} = 6V$ )	Qg	_	27	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	44	_	nC	V <sub>DS</sub> = 60V, I <sub>D</sub> = 25A	
Gate-Source Charge	Qgs		15	_	nc		
Gate-Drain Charge	Q <sub>gd</sub>		9	_			
Turn-On Delay Time	t <sub>D(ON)</sub>		12.5	_			
Turn-On Rise Time	tR	_	13.7	—	1	$V_{DD} = 60V, V_{GS} = 10V$ $I_D = 25A, R_G = 2.7\Omega$	
Turn-Off Delay Time	tD(OFF)	_	24.4	—	ns		
Turn-Off Fall Time	tF	_	10.9	—	]		
Reverse Recovery Time	t <sub>RR</sub>		55	—	ns		
Reverse Recovery Charge	Qrr		105	_	nC	- I <sub>F</sub> = 25A, dI/dt = 100A/μs	

Notes:

Thermal resistance from junction to soldering point (on the exposed drain pad).
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.



### DMT12H007SPS



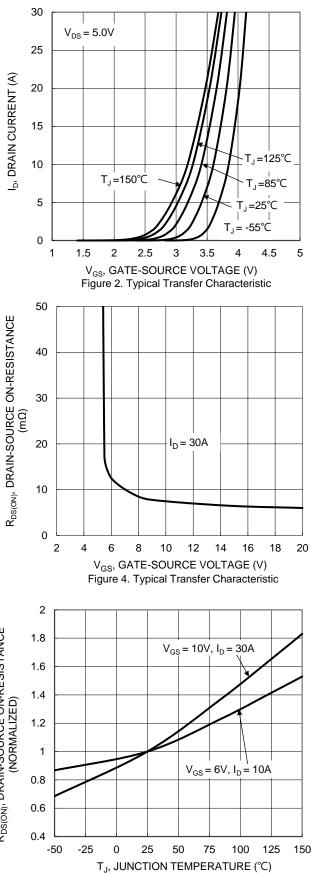
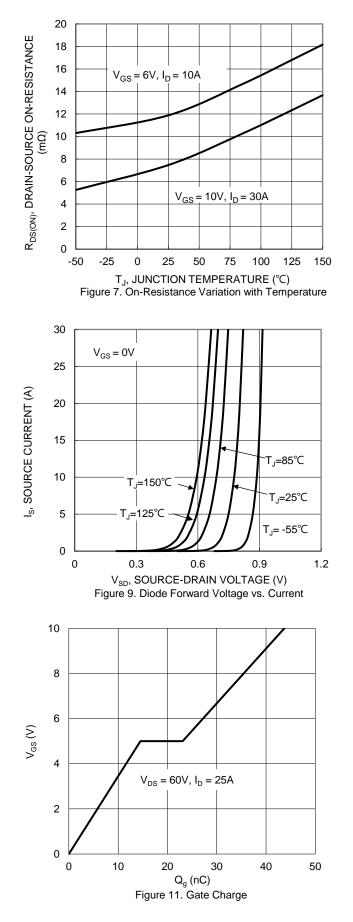
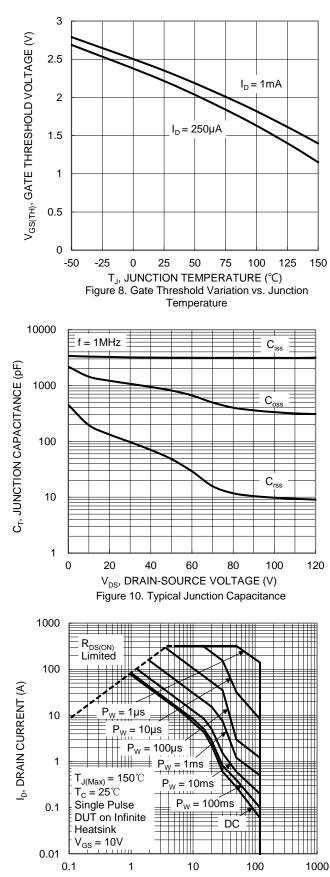


Figure 6. On-Resistance Variation with Temperature







V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area

DMT12H007SPS Document number: DS41427 Rev. 5 - 2



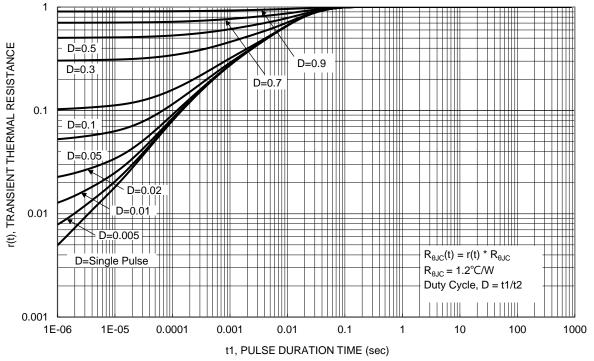
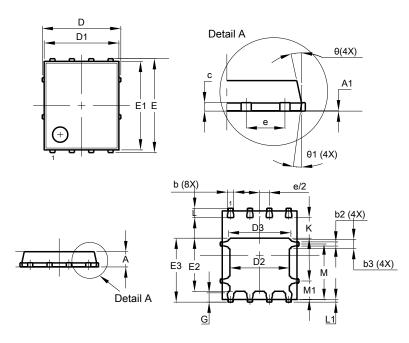


Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

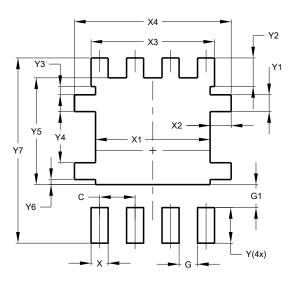


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
c	0.230	0.330	0.277		
D		5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90 4.30 4.10				
ш	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
κ	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

#### PowerDI5060-8



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